



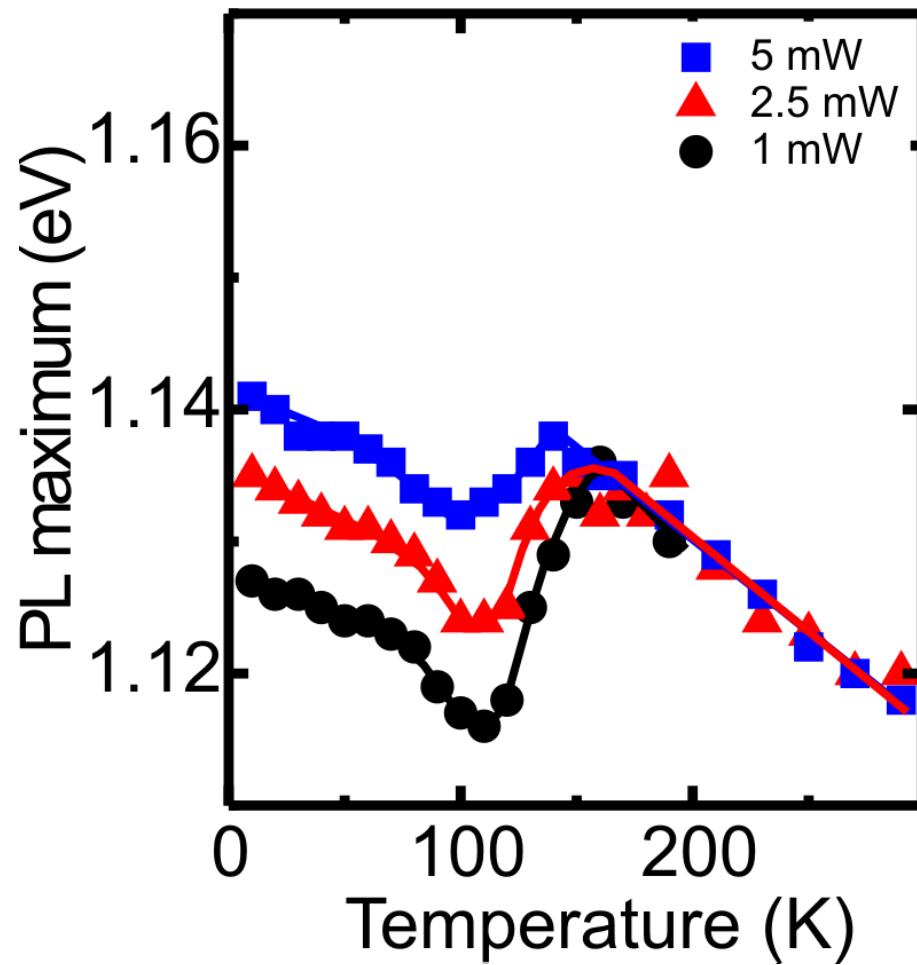
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Clustering Effects in Ga(AsBi)

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Motivation: S-Shape



Imhof et al., Appl. Phys. Lett. 96, 131115 (2010)

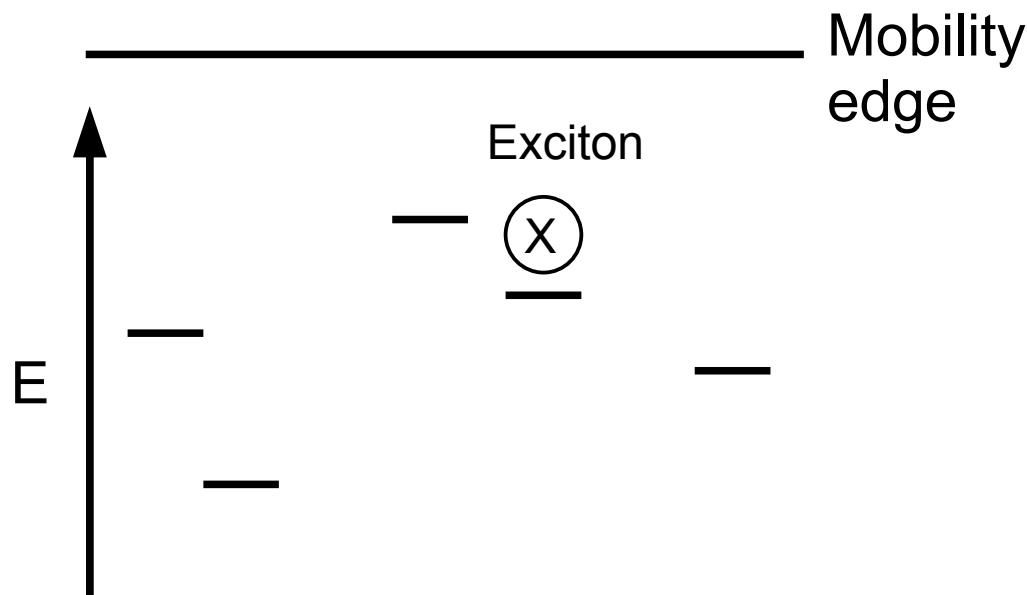


Outline

- Photoluminescence in disorderd semiconductors
- Kinetic Monte-Carlo simulation
- Experimental results
- Two scale approach for Ga(AsBi)
- Conclusion and outlook



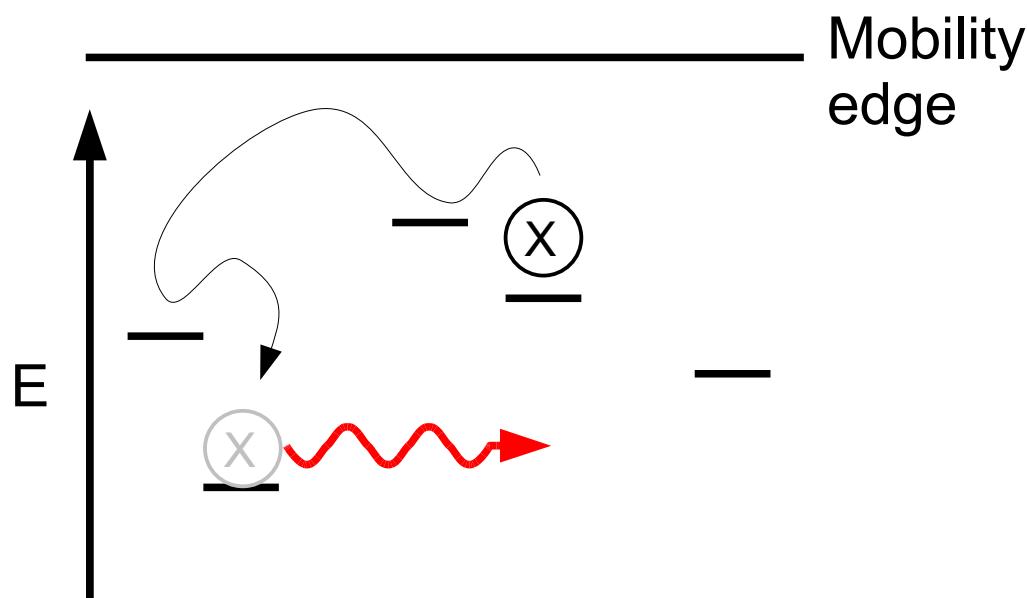
Disorder Model



- Localized states randomly distributed in space
 - N_0 : Area density of localized states
 - α : Exciton localization radius
- Energies given by a certain distribution function



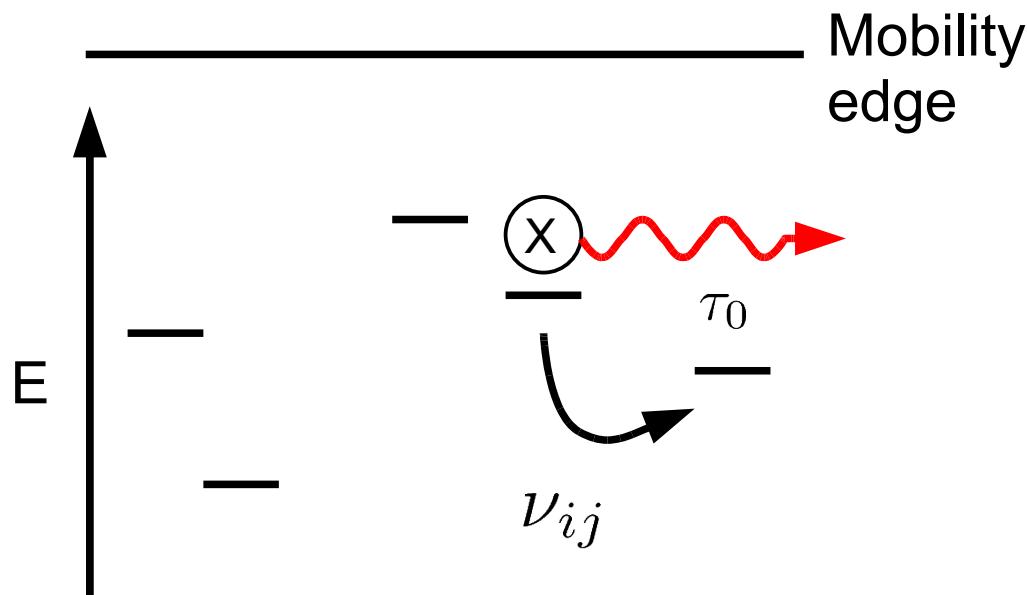
Hopping of Excitons



- Excitons can move among localized states
- Motion of excitons independent in the case of low densities
- Excitons can decay radiatively



Hopping of Excitons

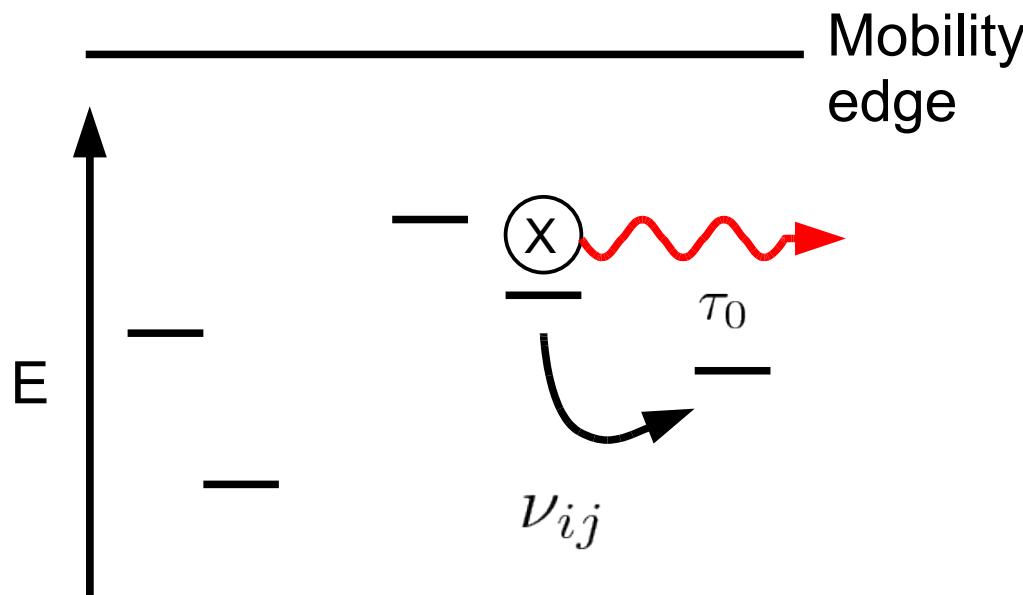


- Hopping transition given by Miller-Abrahams Indices
- Excitons can decay with life time τ_0

$$\nu_{ij} = \nu_0 \exp \left(-\frac{2r_{ij}}{\alpha} - \frac{\epsilon_j - \epsilon_i - |\epsilon_j - \epsilon_i|}{2k_b T} \right)$$



Hopping of Excitons



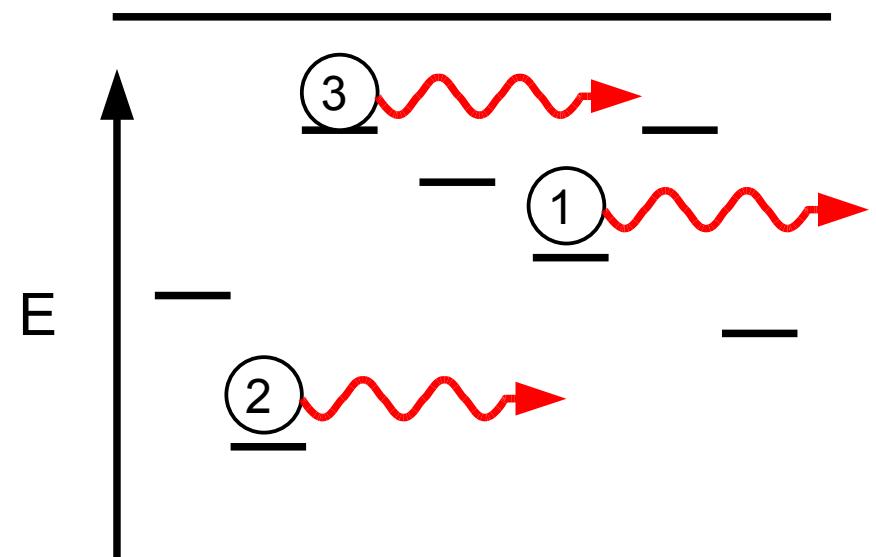
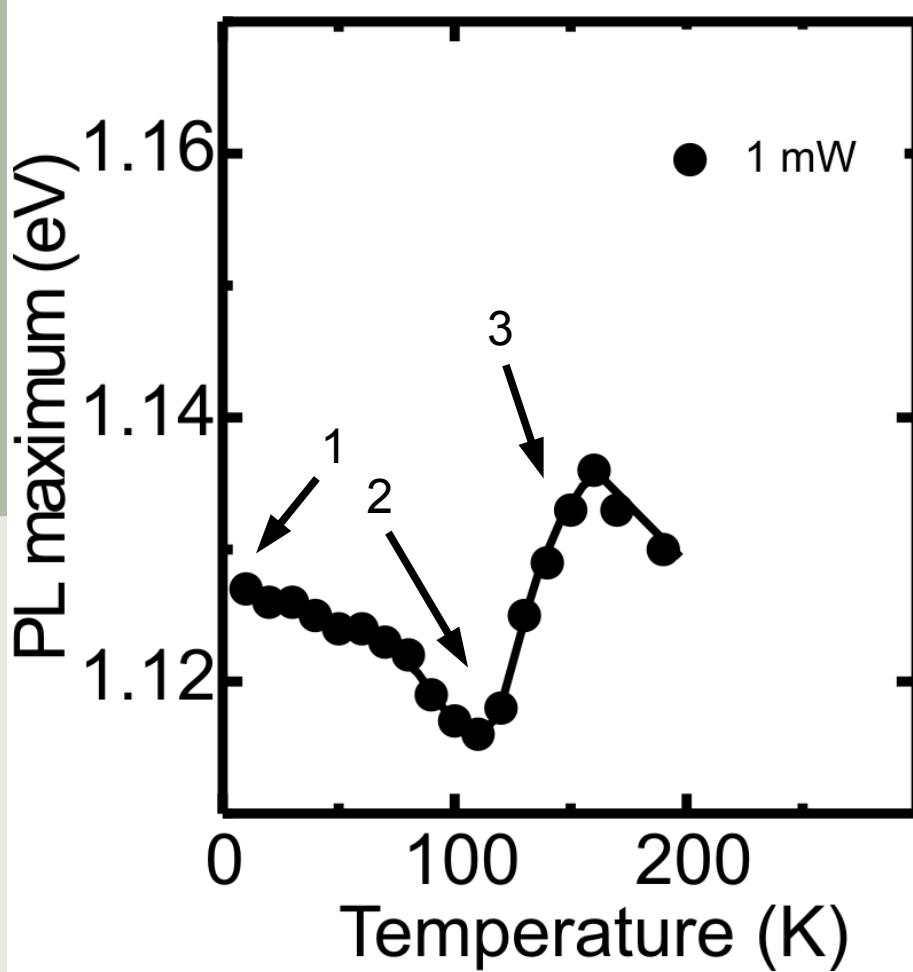
- Dynamic of exciton:
 $t_i^{-1} = -\nu_i \ln \xi$
- Spectra depend on three parameters: $\nu_0 \tau_0$, ϵ_0 , $N_0 \alpha^2$

- Hopping transition given by Miller-Abrahams Indices
- Excitons can decay with life time τ_0
- Decay rate of exciton on i th site:

$$\nu_i = \tau_0^{-1} + \sum_j \nu_{ij}$$



Explanation of the S-Shape



Kinetic Monte-Carlo Simulation

1. Calculate energies and positions of localized states
2. Choose start position of exciton randomly
3. Calculate hopping rates
4. Decide whether exciton decays or performs a hop
 - Decay: save the energy and restart with a new exciton
 - Hopping transition: Go to step 3



Ga(AsBi) Sample Properties

- Thickness ~30nm
- Bi content: 4% - 5%
- Substrate: GaAs
- MBE-grown

Grown by:

D. Beaton

Univ. of British Columbia, Kanada

T. Tiedje

Univ. of Victoria, Kanada

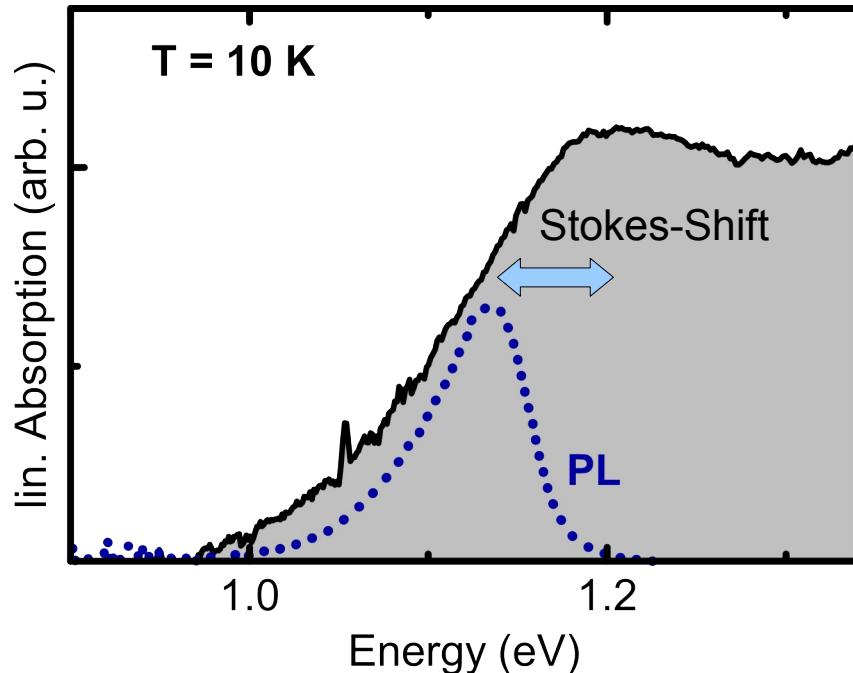
X. Lu

Arizona State University, USA



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Experimental results I



- Band gap from linear absorption spectrum around 1.2 eV
- Gaussian shaped density of states at low energy tail

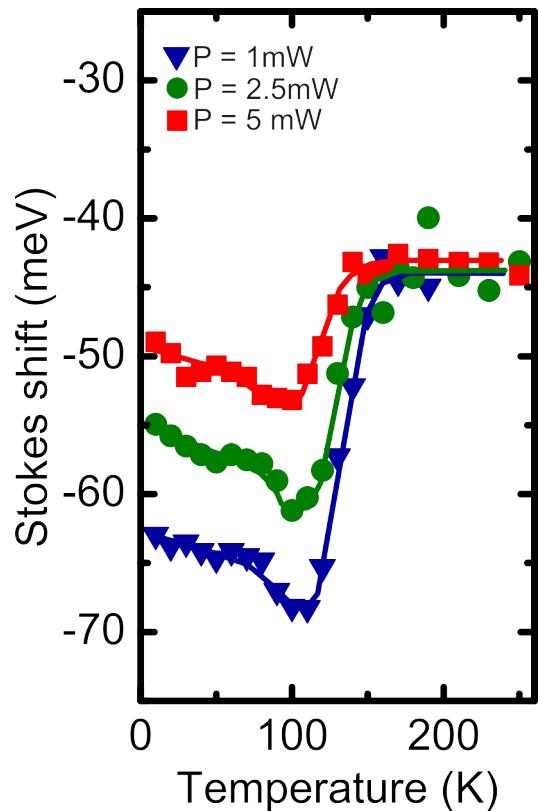
Imhof et al., Appl. Phys. Lett. 96, 131115 (2010)

Experiments done by

A. Chernikov, K. Kolata, N. Köster, M. Koch, S. Chatterjee
Philipps University Marburg, Germany



Experimental results II

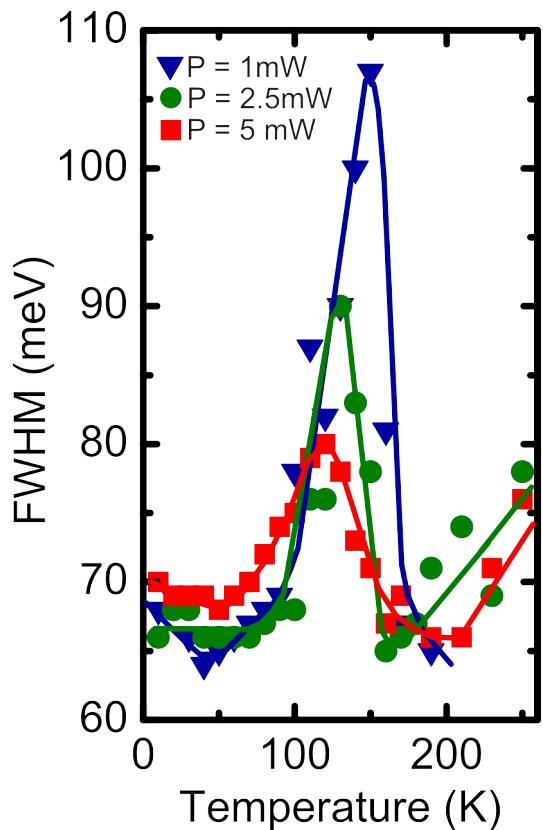


- Zero-temperature Stokes-shift excitation power dependent
- Maximal Stokes-shift around 110 K
- Finite Stokes-shift at high temperatures
 - Disorder effects still present at high temperatures

Imhof et al., Appl. Phys. Lett. 96, 131115 (2010)



Experimental results III



- Very broad PL spectra, FWHM at T=0 around 70 meV
- PL linewidth at T=0 excitation power independent
- FWHM has maximum at 140 K
- Sign of exponential DOS

Imhof et al., Appl. Phys. Lett. 96, 131115 (2010)

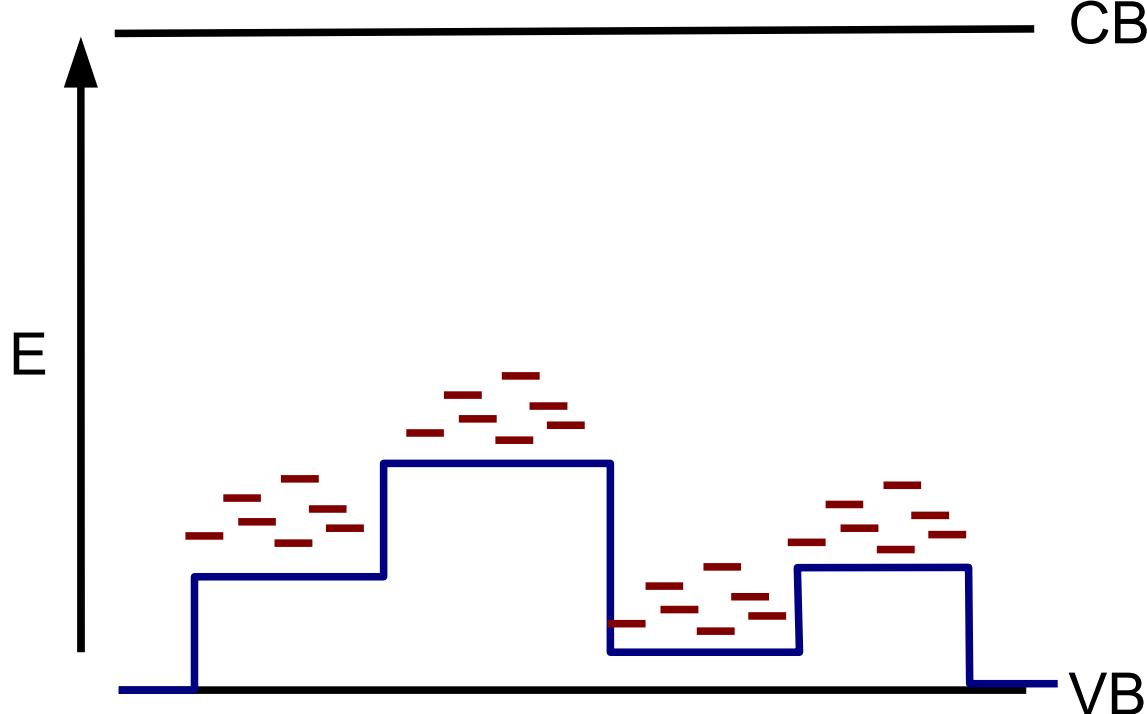


Summary: Experimental results

- Gaussian shaped low energy tail of linear absorption spectra
 - Sign of Gaussian DOS
- Maximum Stokes-shift at T=110 K and maximum FWHM at T=140 K
 - Sign of exponential DOS with energy scale of 11 meV
- Disorder effects still present at high temperatures
 - Inconsistent with energy scale of 11 meV



Two energy scales

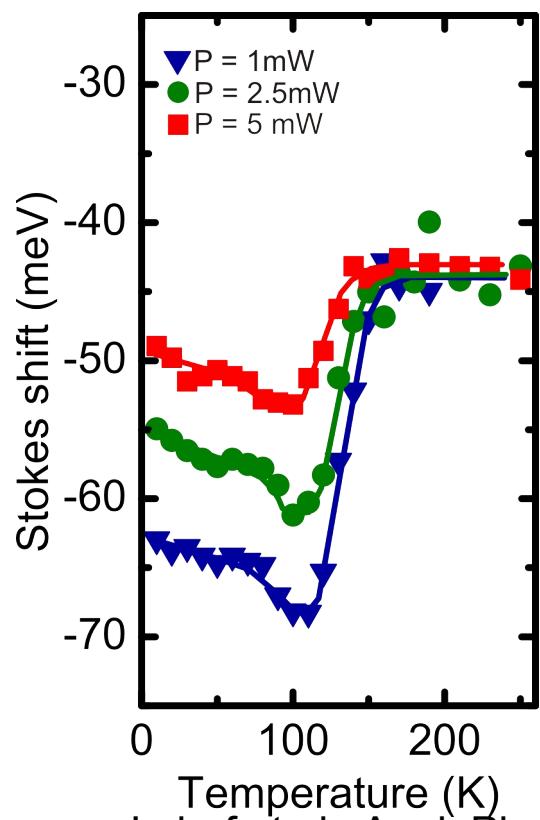


- Alloy disorder of Bi only affects the valence band
 - Gaussian distribution
- Additional Bi-Cluster sites beyond the valence band
 - Exponential distribution

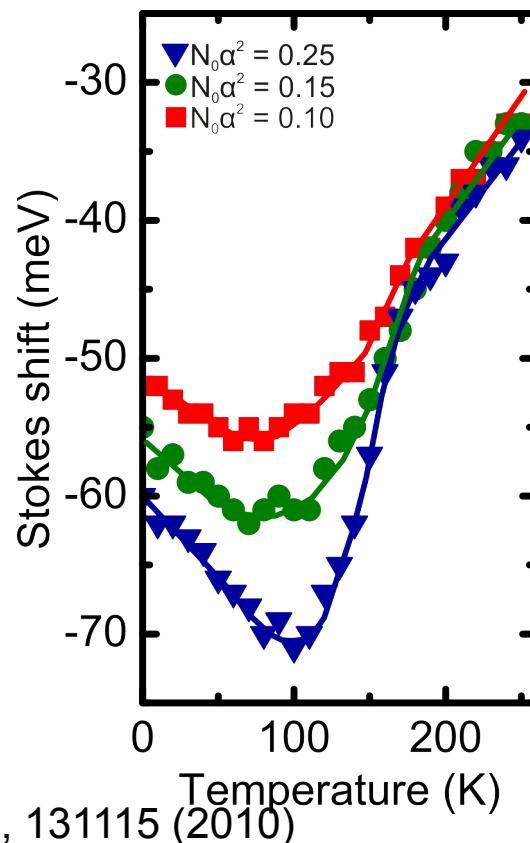


Experiment-Theory Comparison Stokes-Shift

Experiment



Theory

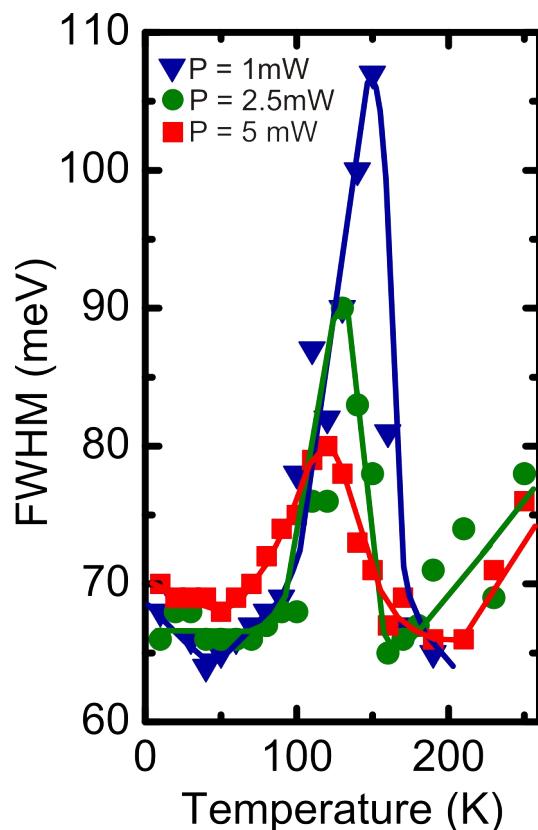


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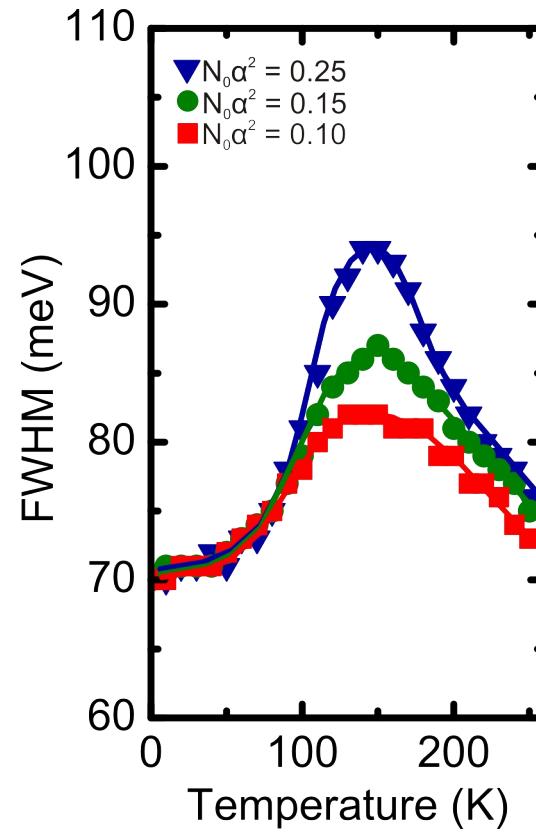


Experiment-Theory Comparison FWHM

Experiment



Theory



Imhof et al., Appl. Phys. Lett. 96, 131115 (2010)



Conclusion and Outlook

- Experimental spectra show both, Gaussian and exponential behavior of DOS
- Spectra can be fitted using the approach of two energy scales
- Next steps:
 - Time dependent photoluminescence spectra
 - Analysis of systematic sample series



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Further Details:
Imhof et al., Appl. Phys. Lett. 96, 131115 (2010)

